

1,550nm Modulator Integrated DFB Laser

FLD5F10NP-A

FEATURES

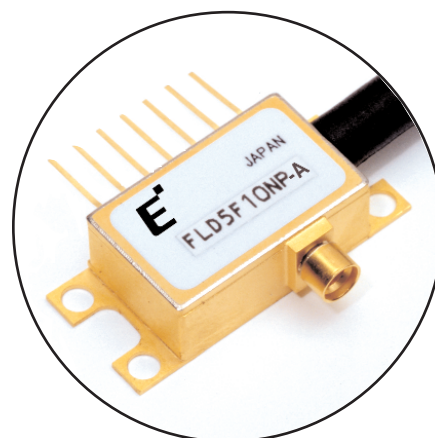
- Modulator Integrated DFB Laser Diode Module
- CW operation of DFB laser section
- Modulation voltage applied only to modulator section
- High speed butterfly package with GPO connection
- Built-in optical isolator, monitor photodiode, thermistor, and thermo-electric cooler

APPLICATION

This MI laser is intended for short reach applications up to 5km (100ps/nm) at 10Gb/s.

DESCRIPTION

The Modulator Integrated DFB Laser (MI DFB Laser) has an electro-absorption modulator monolithically integrated with a conventional Distributed Feed-Back (DFB). The modulation voltage is applied to the modulator section while the laser section operates CW allowing extremely low wave length chirping. Extinction ratios of more than 8.3 dB can be achieved with 2.6 Vp-p modulation. The MI laser is installed in a butterfly type package. The module incorporates a highly stable optical coupling system. The module includes an optical isolator, monitor photodiode, thermistor and a thermo-electric cooler.



ABSOLUTE MAXIMUM RATINGS (T_{op}=25°C, unless otherwise specified)

Parameter	Symbol	Condition	Rating		Unit
			Min.	Max.	
Operating Case Temperature	T _{op}	-	-20	+70	°C
Storage Temperature	T _{stg}	-	-40	+85	°C
Optical Output Power	P _f	CW	-	5	mW
Laser Forward Current	I _F	CW	-	150	mA
Laser Reverse Voltage	V _R	CW	-	2	V
Modulator Forward Voltage	V _m	CW	-5	+1	V
Photodiode Forward Current	-	-	-	1	mA
Photodiode Reverse Voltage	V _{DR}	-	-	10	V
TEC Voltage	V _c	Cooling	-	+2.5	V
		Heating	-2.5	-	
TEC Current	I _c	Cooling	-	+1.4	A
		Heating	-0.9	-	
Thermistor Temperature	T _{th}	ATC Operation	-20	+70	°C
Lead Soldering Time	-	260°C	-	10	sec

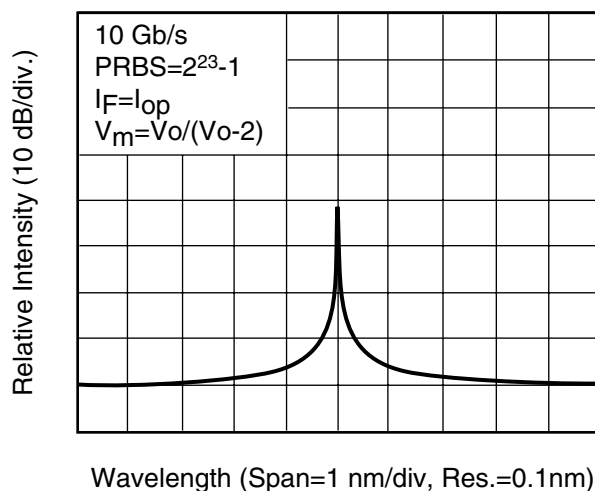
OPTICAL & ELECTRICAL CHARACTERISTICS (T_L = T_{set}, T_c = 25°C, BOL, unless otherwise specified)

Parameter	Symbol	Test Condition	Limits			Unit
			Min.	Type	Max.	
Peak Wavelength	λ_p	Note (2)	1530	-	1565	nm
Threshold Current	I _{th}	CW, V _m =V _o	-	-	30	mA
Operating Current	I _{op}	CW, V _m =V _o	50	-	100	mA
Forward Voltage	V _F	CW, I _F =I _{op} , V _m =V _o	-	1.4	2.0	V
Optical Output Power (Avg. Power)	P _f	Note (1)	-2	-	-	dBm
Dispersion Penalty	dP	Note (1)	-	-	1.0	dB
Sidemode Suppression Ratio	SSR	Note (2)	35	-	-	dB
Extinction Ratio	R _{ext}	f=10Gb/s, I _F =I _{op} , V _m =V _o /(V _o -V _{mod})	8.3	-	-	dB
Optical Isolation	I _s	T _c = -20 to +65°C	25	35	-	dB
On Level Modulation	V _o	-	-0.7	-	0	V
Modulator Drive Voltage	V _{mod}	(V _o -V _{mod})>=-3.3V, R _{ext} =8.3dB	-	-	2.6	V
Rise Time	T _r	Note (2), 20 to 80%	-	-	40	ps
Fall Time	T _f	Note (2), 20 to 80%	-	-	40	ps
Cut-off Frequency	S ₂₁	-3dB bandwidth, V _m =V _o -0.5(V _{mod}), I _F =I _{op}	10	-	-	GHz
RF Return Loss	S ₁₁	f=DC-5GHz, 50Ω Test Set, V _m =V _o , I _F =I _{op}	8	-	-	dB
RF Return Loss	S ₁₁	f=5-10GHz, 50Ω Test Set, V _m =V _o , I _F =I _{op}	3	-	-	dB
Relative Intensity Noise	RIN	f=10 GHz, V _m =V _o , I _F =I _{op} , ORL=>24dB	-	-	-120	dB/Hz
TEC Capacity	ΔT	P _{TEC} =2.4W, I _F =I _{op}	45	-	-	°C
TEC Current	I _c	I _F =I _{op} , ΔT=45°C	-	-	1.0	A
TEC Voltage	V _c	I _F =I _{op} , ΔT=45°C	-	-	2.4	V
TEC Power Dissipation	P _c	I _F =I _{op}	-	-	2.4	W
Thermal Resistance	R _{th}	T _L =25°C	9.5	10.0	10.5	kΩ
Thermistor B Constant	B		3,270	3,450	3,630	K

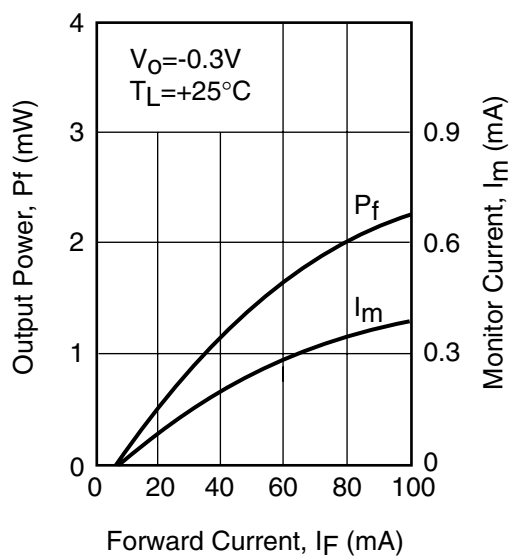
Note (1) Eudyna Test System
9.95328Gb/s, PRBS=2⁻²³-1, I_F=I_{op}, V_m=V_o and (V_o-V_{mod})
Dispersion=100ps/nm, Dispersion penalty at
Bit Error Rate = 1.0E-10

Note (2) Eudyna Test System
9.95328Gb/s, PRBS=2⁻²³-1, I_F=I_{op}, V_m=V_o and (V_o-V_{mod})

Fig. 1 Lasing Spectrum



**Fig. 2 Forward Current vs. Output Power and
Forward Current vs. Forward Voltage**



**Fig. 3 Extinction Ratio
vs. Modulation Voltage**

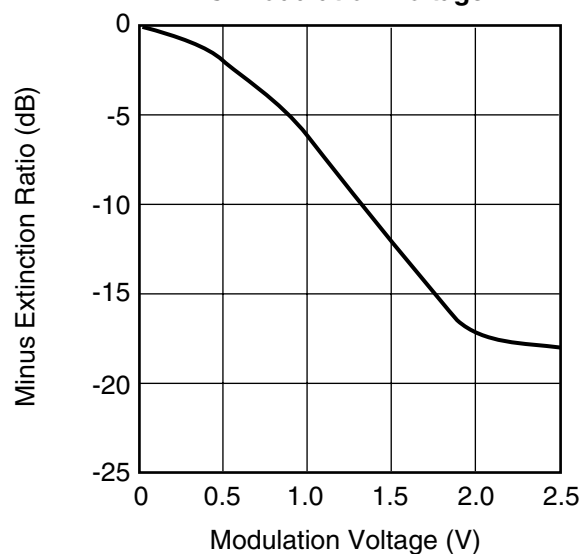


Fig. 4 Cut-off Frequency (S21)

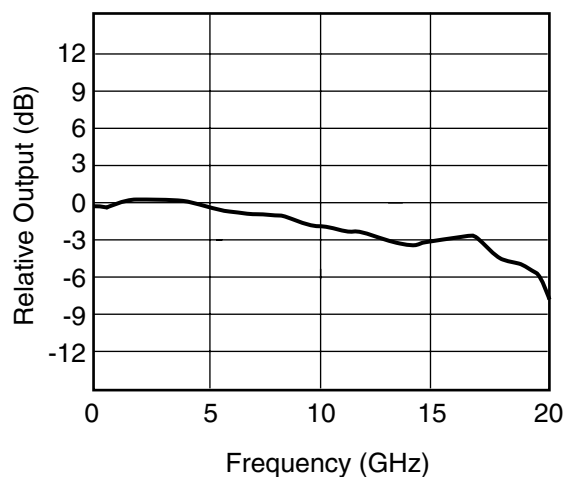


Fig. 5 RF Return Loss (S11)

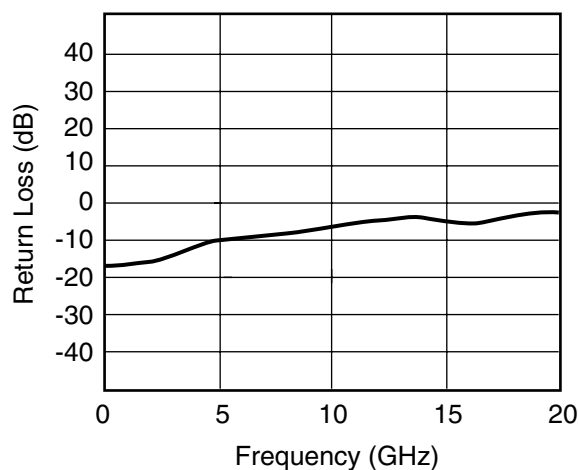
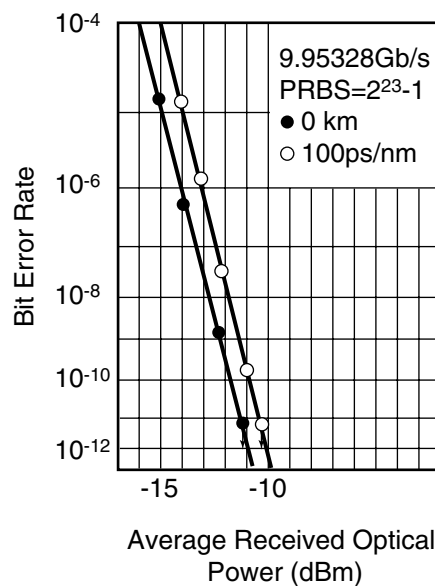
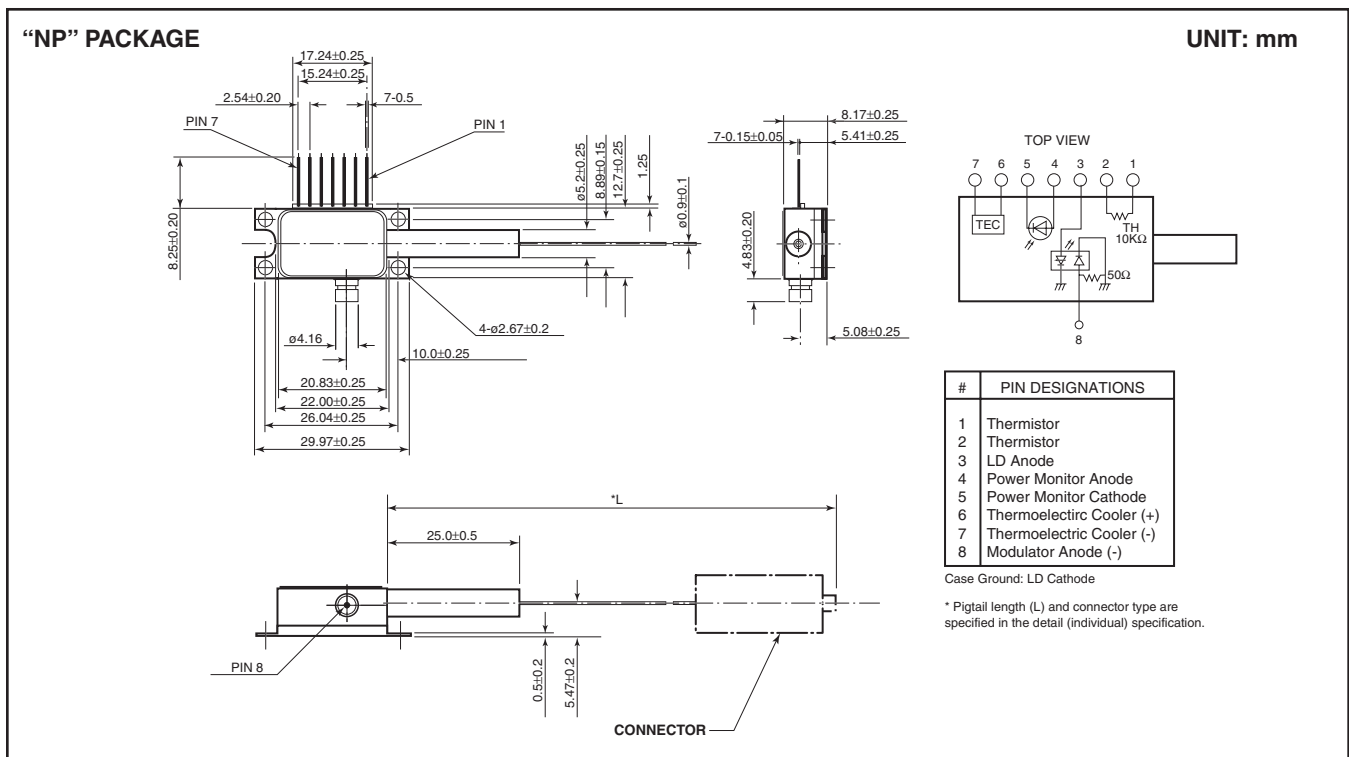


Fig. 6 Transmission Characteristics



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